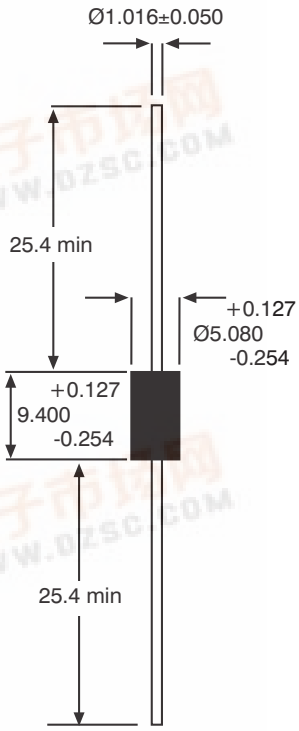
T10B series Sibod™

FEATURES

- Glass passivated junction
- High current diverting capability 250A
- Low capacitance, less than 200pF
- UL recognized
- Automatic reset
- Does not degrade

APPLICATION

- Bi-directional device for telephone and line card protection



All dimensions in mm

ELECTRICAL CHARACTERISTICS (Tamb = +25°C)

SYMBOL	PARAMETER
V_{RM}	Stand-off Voltage
V_{BR}	Breakdown Voltage
I_H	Holding Current
V_R	Continuous Reverse Voltage

ABSOLUTE RATINGS (limiting values) (Tj = + 25°C) L = 10mm

SYMBOL	PARAMETER		VALUE	UNIT
P	Power dissipation on infinite heatsink	Tamb = 50°C	5	W
Ipp	Peak Pulse Current	10x1000µsec 10/700 1.5KV 8-20 us expo	100 125 250	A
I_{tsm}	Non-repetitive surge peak on-state current	tp = 20 ms	50	A
di/dt	Critical rate of rise of on-state current	Non repetitive	100	A/us
T stg Tj	Storage and operating junction Temperature range		-40 to 150 150	°C °C
Tl	Maximum lead temperature for soldering during 10s at 4mm from case		230	°C

THERMAL RESISTANCES

SYMBOL	PARAMETER		VALUE	UNIT
Rth(j-i) Rth(j-a)	Junction-leads on infinite heatsink Junction-ambient on printed circuit	L = 10mm	20 75	°C/W °C/W

All parameters are tested using Fet Test ™ Model 3600

DEVICE TYPE	I_{RM} @ V_{RM} max		I_R @ V_R max		V_{BO} @ I_{BO} max		I_H min	C typ
	µA	V	µA	V	V	mA	mA	pF
T10B035	2	32	50	35	55	800	150	180
T10B065	2	55	50	65	80	800	150	160
T10B120	2	110	50	120	160	800	150	140
T10B140	2	120	50	140	200	800	150	140
T10B200	2	170	50	200	265	800	150	130
T10B230	2	200	50	230	300	800	150	120
T10B270	2	230	50	270	350	800	150	120

ORDERING INFORMATION

T10B _ _ _ _ _

Voltage

Holding Current Option

Packaging Option

B = Bulk (500 pcs)

T = Tape and reeled (1500 pcs)